



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>



NTE639 General Purpose Silicon Rectifier High Voltage, Standard Recovery DO201AD Type Package

Features:

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Maximum Ratings and Electrical Characteristics:

($T_A = +25^\circ\text{C}$ unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Maximum Peak Repetitive Reverse Voltage, V_{RRM}	1300V
Maximum Working Peak Reverse Voltage, V_{RWM}	1300V
Maximum DC Blocking Voltage, V_R	1300V
Maximum RMS Reverse Voltage, $V_{R(RMS)}$	910V
Maximum Average Rectified Output Current (.375" (9.5mm) Lead Length, $T_A = +75^\circ\text{C}$), I_O	3A
Non-Repetitive Peak Forward Surge Current, I_{FSM} (8.3ms Single Half Sine-Wave Superimposed on Rated Load)	200A
Maximum Instantaneous Forward Voltage ($I_F = 3A$), V_{FM}	1.0V
Maximum Peak Reverse Current ($V_R = 1300V$), I_{RM} $T_A = +25^\circ\text{C}$	5° A
$T_A = +100^\circ\text{C}$	100° A
Typical Junction Capacitance (Note 1), C_j	50pF
Operating Junction Temperature Range, T_J	-65° to +125°C
Storage Temperature Range, T_{stg}	-65° to +150°C
Typical Thermal Resistance, Junction-to-Ambient, R_{thJA} (.375" (9.5mm) Lead Length, $T_A = +25^\circ\text{C}$)	20°C/W

Note 1. Measured at 1MHz and applied reverse voltage of 4V.

